TOSHIBA ALLOY-FREE HIGHT SPEED THYRISTOR

## S H 4 O O R 2 9 B

HIGH POWER CONTROL APPLICATIONS

Repetitive Peak Off-State Voltage :  $V_{DRM}$  = 1300V

Repetitive Peak Reverse Voltage : VRRM

Average On-State Current  $: I_{T(AV)} = 400A$ Turn-Off Time :  $t_0 = 25 \mu s$  (Max.)

Critical Rate of Rise of On-State Current

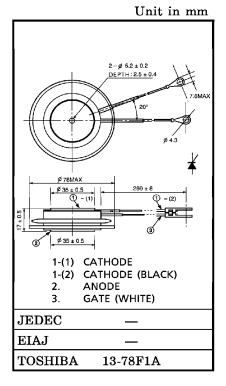
:  $di/dt = 200A/\mu s$ 

Critical Rate of Rise of Off-State Voltage

:  $dv/dt = 500V/\mu s$ 

Weight : 260g

Flat Package



The information contained herein is subject to change without notice.

1997-10-07 1/4

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## **MAXIMUM RATINGS**

CHARACTERISTIC	SYMBOL	RATING	UNIT	
Repetitive Peak Off-State Voltage and Repetitive Peak Reverse Voltage	${ m v_{DRM}} \ { m v_{RRM}}$	1300	v	
Non-Repetitive Peak Reverse Voltage (Non-Repetitive $< 5$ ms, $T_j = 0 \sim 125$ °C)	$v_{ m RSM}$	1400	v	
R.M.S On-State Current	IT (RMS)	628	Α	
Average On-State Current	I <sub>T</sub> (AV)	400	A	
Peak One Cycle Surge On-State Current (Non-Repetitive)	I <sub>TSM</sub>	7200 (50Hz) 8000 (60Hz)	V	
I <sup>2</sup> t Limit Value	${f I^2 t}$	$200 \times 10^{3}$	$\mathrm{A}^2\mathrm{s}$	
Critical Rate of Rise of On-State Current (Note)	di / dt	200	A/μs	
Peak Gate Power Dissipation	$P_{GM}$	20	W	
Average Gate Power Dissipation	PG (AV)	4	W	
Peak Forward Gate Current	$I_{GM}$	4	Α	
Peak Forward Gate Voltage	$v_{FGM}$	20	V	
Peak Reverse Gate Voltage	$v_{RGM}$	5	V	
Junction Temperature	$T_{ m j}$	-40~115	°C	
Storage Temperature Range	$\mathrm{T_{stg}}$	-40~115	$^{\circ}\mathrm{C}$	
Mounting Force	_	$14.7 \pm 1.5$	kN	

Note : V\_D=1/2 Rated, T\_j=110°C, Gate Supply (V\_G=15V, R\_G=8\Omega, t\_r  $\! \leq \! 1 \mu s$ )

## **ELECTRICAL CHARACTERISTICS**

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	MAX.	UNIT
Repetitive Peak Off-State Current and Repetitive Peak Reverse Current	IDRM IRRM	$V_{ m DRM} = V_{ m RRM} = { m Rated}$ $T_{ m j} = 115 { m ^{\circ}C}$	_	50	mA
Peak On-State Voltage	$v_{TM}$	$I_{TM} = 1250A, T_j = 25^{\circ}C$	_	2.2	V
Gate Trigger Voltage	$v_{GT}$	$T_{j} = -40^{\circ}C$ $T_{j} = 25^{\circ}C$	<u> </u>	4.5 3.5	V
Gate Trigger Current	$I_{\mathrm{GT}}$	$V_D = 6V, R_L = 6\Omega$ $T_j = -40^{\circ}C$ $T_j = 25^{\circ}C$		400 260	mA
Gate Non-Trigger Voltage	$v_{\mathrm{GD}}$	T 1/0 D / 1 M 11500		<u> </u>	V
Gate Non-Trigger Current	$_{ m I_{GD}}$	$V_D=1/2$ Rated, $T_j=115$ °C	5	_	mA
Delay Time	t <sub>d</sub>	V <sub>D</sub> =1/2 Rated, T <sub>j</sub> =25°C		4	μs
Gate Turn-On Time	t <sub>gt</sub>	Gate Supply $(V_G=15V, R_G=8\Omega, t_r\leq 1\mu s)$	_	6	μs
Turn-Off Time	$\mathbf{t_q}$	$I_{TM}$ =800A, $V_R \ge 50V$ $dv/dt$ =20V/ $\mu$ s, $T_j$ =110°C $V_{DRM}$ =1/2 Rated	_	25	μs
Holding Current	${ m I_{H}}$	$T_j=25$ °C, $R_L=6\Omega$	_	400	mA
Critical Rate of Rise of Off-State Voltage	dv / dt	V <sub>DRM</sub> =1/2 Rated, T <sub>j</sub> =115°C Gate Open, Exponential Rise			V/μs
Thermal Resistance (Junction to Case)	$ m R_{th~(j-f)}$	DC	_	0.04	°C/W

